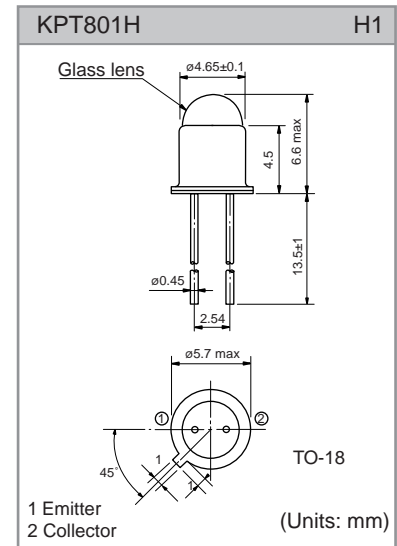


Features

- NPN phototransistor packaged in a 2 leads TO-18
- Glass lens
- Low leak current

Applications

- Optical switches
- Optical encoders
- Photo-isolator
- Camera stroboscopes
- Infrared sensors
- Automatic control apparatus



Maximum ratings

Item	Symbol	Value	Units
Collector•Emitter Vol.	V_{ceo}	20	V
Emitter•Collector Vol.	V_{eco}	5	V
Collector•Base Vol.	V_{cbo}	-	V
Emitter•Base Vol.	V_{ebo}	-	V
Operating Temperature	T_{opr}	-25 ~ +125	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C

Characteristics ($T_a=25\text{ }^\circ\text{C}$ unless otherwise noted.)

Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Active Area	S	0.64x0.64			mm	
Operating Voltage	V_{RO}	5			V	
Sensitive Wavelength		400	800(ρ)	1000	nm	ρ = Peak wavelength
Photocurrent	I_L		2		mA	$V_{ce}=5V$, 100lux(@2856K)
Dark Current	I_{ceo}		100	200	nA	$V_{ce}=20V$
Current Amplification Factor	h_{FE}	600				$V_{ce}=5V$, $I_c=2mA$
Collector•Emitter Saturation Voltage	$V_{ce(sat)}$			0.4	V	$I_c=0.1mA$
Rise/Fall Time	t_r, t_f		5		μs	$V_{ce}=5V$, $I_c=2mA$, $R_L=100\ \Omega$

KPT801H

